M76DW63000A
M76DW62000A

64Mbit (x8/ x16, Multiple Bank, Boot Block) Flash Memory and 8Mbit/4Mbit SRAM, 3V Supply, Multiple Memory Product

PRELIMINARY DATA

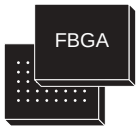
FEATURES SUMMARY

- MULTIPLE MEMORY PRODUCT
  - 64 Mbit (8Mb x8 or 4Mb x16), Multiple Bank, Page, Boot Block, Flash Memory
  - SRAM: 8Mbit (512K x 16) for M76DW63000A, or 4Mbit (256K x 16) for M76DW62000A
- SUPPLY VOLTAGE
  - V_{CCF} = V_{CCS} = 2.7V to 3.3V
  - V_{PPF} = 12V for Fast Program (optional)
- ACCESS TIME: 70, 90ns
- LOW POWER CONSUMPTION
- ELECTRONIC SIGNATURE
  - Manufacturer Code: 0020h
  - Device Code: 227Eh + 2202h + 2201h

FLASH MEMORY

- ASYNCHRONOUS PAGE READ MODE
  - Page Width: 4 Words
  - Page Access: 25, 30ns
  - Random Access: 70, 90ns
- PROGRAMMING TIME
  - 10µs per Byte/Word typical
  - 4 Words/ 8 Bytes at-a-time Program
- MEMORY BLOCKS
  - Quadruple Bank Memory Array: 8Mbits + 24Mbits + 24Mbits + 8Mbits
  - Parameter Blocks (at both Top and Bottom)
- DUAL OPERATIONS
  - While Program or Erase in a group of banks (from 1 to 3), Read in any of the other banks
- PROGRAM/ERASE SUSPEND and RESUME MODES
  - Read from any Block during Program Suspend
  - Read and Program another Block during Erase Suspend
- UNLOCK BYPASS PROGRAM COMMAND
  - Faster Production/Batch Programming

Figure 1. Package



LFBGA73 (ZA)
8 x 11.6mm

- $V_{PP}/\overline{WP}$ PIN for FAST PROGRAM and WRITE PROTECT
- TEMPORARY BLOCK UNPROTECTION MODE
- COMMON FLASH INTERFACE
  - 64 bit Security Code
- EXTENDED MEMORY BLOCK
  - Extra block used as security block or to store additional information
- 100,000 PROGRAM/ERASE CYCLES per BLOCK

SRAM

- 8Mbit (512K x 16) or 4Mbit (256K x 16)
- ACCESS TIME: 70ns
- LOW V_{CCS} DATA RETENTION: 1.5V
- POWER DOWN FEATURES USING TWO CHIP ENABLE INPUTS

TABLE OF CONTENTS

SUMMARY DESCRIPTION

The M76DW62000A is a low voltage Multiple Memory Product which combines two memory devices; a 64 Mbit Multiple Bank, Boot Block Flash memory (M29DW640D) and an 8 or 4Mbit SRAM. This document should be read in conjunction with the M29DW640D datasheet.

Recommended operating conditions do not allow both the Flash and SRAM devices to be active at the same time.

The memory is offered in an LFBGA73 (8 x 11.6mm, 0.8 mm pitch) package and is supplied with all the bits erased (set to '1').

Figure 2. Logic Diagram

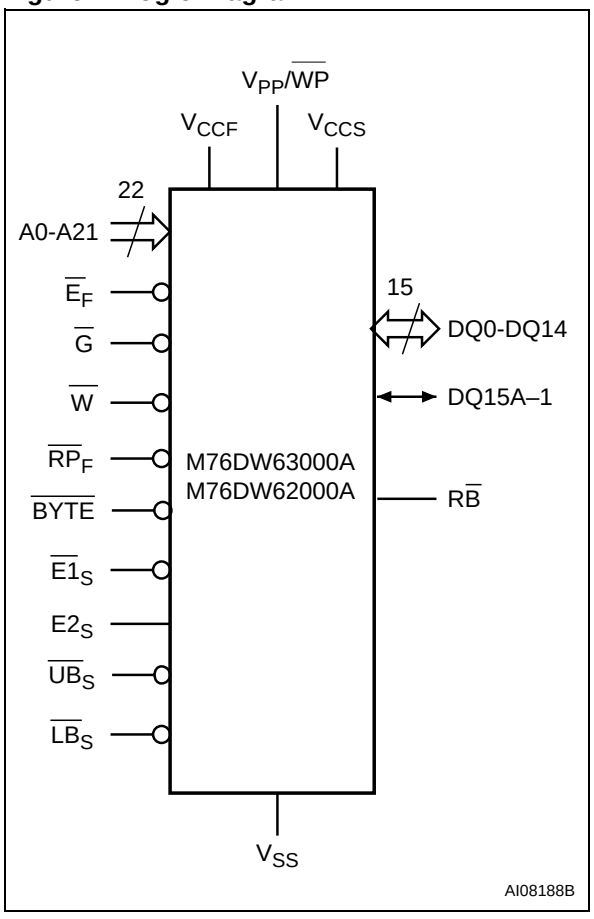
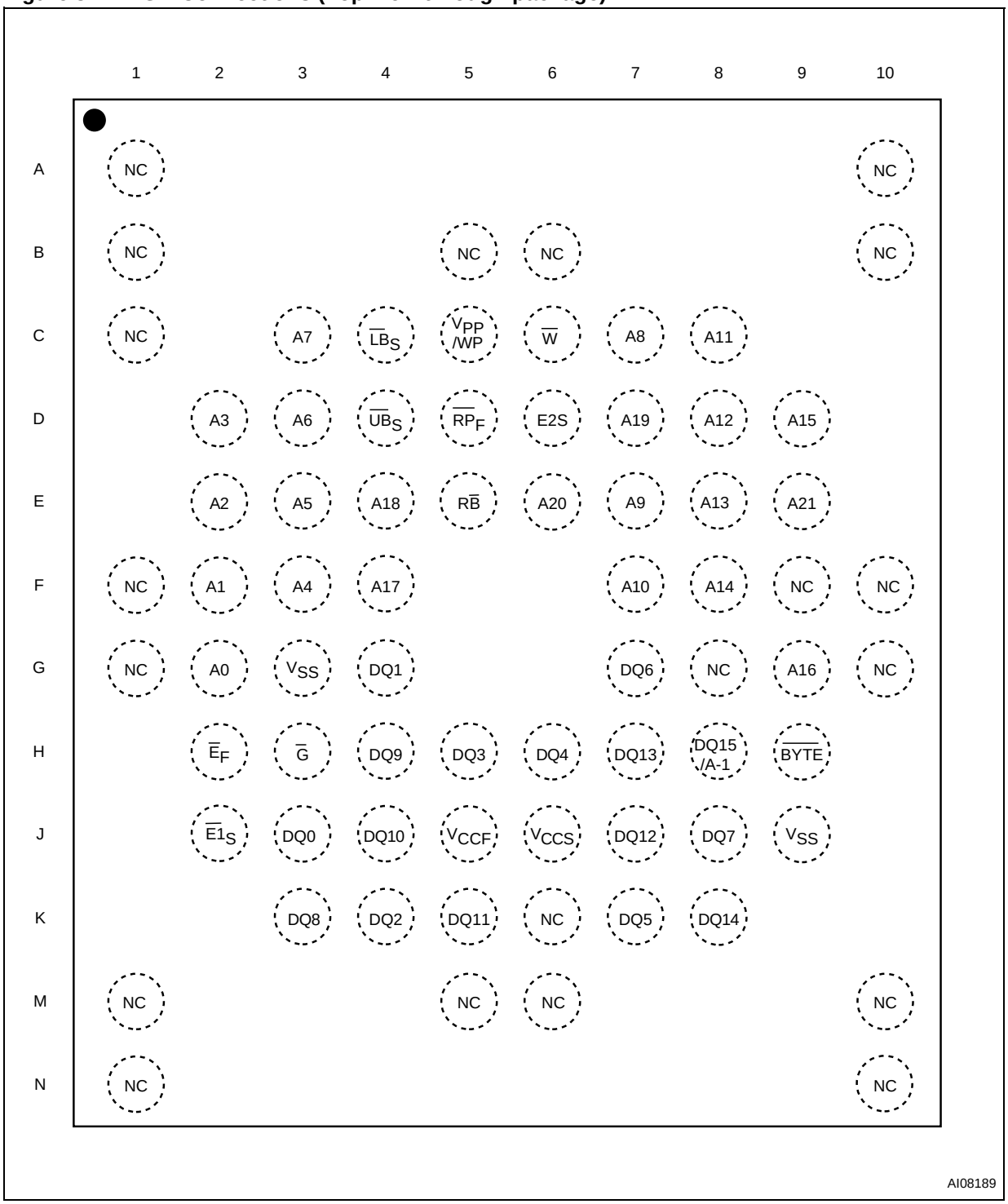


Table 1. Signal Names

A0-A21[1]	Address Inputs
DQ0-DQ7	Data Inputs/Outputs
DQ8-DQ14	Data Inputs/Outputs
DQ15A–1	Data Input/Output or Address Input
$\overline{G}$	Output Enable input
$\overline{W}$	Write Enable input
V_{CCF}	Flash Power Supply
$V_{PP}/\overline{WP}$	V_{PP}/Write Protect
V_{SS}	Ground
V_{CCS}	SRAM Power Supply
V_{SSS}	SRAM Ground
NC	Not Connected Internally
Flash Memory Control Functions	
$\overline{E}_F$	Chip Enable input
$\overline{RP}_F$	Reset/Block Temporary Unprotect
$R\overline{B}$	Ready/Busy Output
$\overline{BYTE}$	Byte/Word Organization Select
SRAM Control Functions	
$\overline{E1}_S$, $E2_S$	Chip Enable inputs
$\overline{UB}_S$	Upper Byte Enable input
$\overline{LB}_S$	Lower Byte Enable input

Note: 1. A21-A19 are not connected to the SRAM component of the M76DW63000A, and A21-A18 are not connected to the SRAM component of the M76DW62000A.

Figure 3. LFBGA Connections (Top view through package)



SIGNAL DESCRIPTION

See Figure 2 Logic Diagram and Table 1,Signal Names, for a brief overview of the signals connected to this device.

Address Inputs (A0-A21). Addresses A0-A18 (for M76DW63000A), or A0-A17 (for M76DW62000A), are common inputs for the Flash Memory and the SRAM components. The other lines (A19-A21, or A18-21, respectively) are inputs for the Flash Memory component only.

The Address Inputs select the cells in the memory array to access during Bus Read operations. During Bus Write operations they control the commands sent to the Command Interface of the internal state machine. The Flash memory is accessed through the Chip Enable ($\overline{E}_F$) and Write Enable ($\overline{W}$) signals, while the SRAM is accessed through two Chip Enable signals ($\overline{E1}_S$ and $E2_S$) and the Write Enable signal ($\overline{W}$).

Data Inputs/Outputs (DQ0-DQ7). The Data I/O outputs the data stored at the selected address during a Bus Read operation. During Bus Write operations they represent the commands sent to the Command Interface of the Program/Erase Controller.

Data Inputs/Outputs (DQ8-DQ14). The Data I/O outputs the data stored at the selected address during a Bus Read operation when $\overline{BYTE}$ is High, V_{IH}. When $\overline{BYTE}$ is Low, V_{IL}, these pins are not used and are high impedance. During Bus Write operations the Command Register does not use these bits. When reading the Status Register these bits should be ignored.

Data Input/Output or Address Input (DQ15A–1). When $\overline{BYTE}$ is High, V_{IH}, this pin behaves as a Data Input/Output pin (as DQ8-DQ14). When $\overline{BYTE}$ is Low, V_{IL}, this pin behaves as an address pin; DQ15A–1 Low will select the LSB of the addressed Word, DQ15A–1 High will select the MSB. Throughout the text consider references to the Data Input/Output to include this pin when $\overline{BYTE}$ is High and references to the Address Inputs to include this pin when $\overline{BYTE}$ is Low except when stated explicitly otherwise.

Flash Chip Enable ($\overline{E}_F$). The Chip Enable input activates the memory, allowing Bus Read and Bus Write operations to be performed. When Chip Enable is High, V_{IH}, all other pins are ignored.

Output Enable ($\overline{G}$). The Output Enable, $\overline{G}$, controls the Bus Read operation of the device.

Write Enable ($\overline{W}$). The Write Enable, $\overline{W}$, controls the Bus Write operation of the device.

V_{PP}/Write Protect ($V_{PP}/\overline{WP}$). The V_{PP}/Write Protect pin provides two functions. The V_{PP} function allows the Flash memory to use an external high voltage power supply to reduce the time required for Program operations. This is achieved by bypassing the unlock cycles and/or using the multiple Word (2 or 4 at-a-time) or multiple Byte Program (2, 4 or 8 at-a-time) commands. The Write Protect function provides a hardware method of protecting the four outermost boot blocks (two at the top, and two at the bottom of the address space).

When V_{PP}/Write Protect is Low, V_{IL}, the memory protects the four outermost boot blocks; Program and Erase operations in these blocks are ignored while V_{PP}/Write Protect is Low, even when $\overline{RP}_F$ is at V_{ID}.

When V_{PP}/Write Protect is High, V_{IH}, the memory reverts to the previous protection status of the four outermost boot blocks (two at the top, and two at the bottom of the address space). Program and Erase operations can now modify the data in these blocks unless the blocks are protected using Block Protection.

When V_{PP}/Write Protect is raised to V_{PP} the memory automatically enters the Unlock Bypass mode. When V_{PP}/Write Protect returns to V_{IH} or V_{IL} normal operation resumes. During Unlock Bypass Program operations the memory draws I_{PP} from the pin to supply the programming circuits. See the description of the Unlock Bypass command in the Command Interface section. The transitions from V_{IH} to V_{PP} and from V_{PP} to V_{IH} must be slower than t_{VHVPP}. See the M29DW640D datasheet for more details.

Never raise V_{PP}/Write Protect to V_{PP} from any mode except Read mode, otherwise the memory may be left in an indeterminate state.

The V_{PP}/Write Protect pin must not be left floating or unconnected or the device may become unreliable. A 0.1µF capacitor should be connected between the V_{PP}/Write Protect pin and the V_{SS} Ground pin to decouple the current surges from the power supply. The PCB track widths must be sufficient to carry the currents required during Unlock Bypass Program, I_{PP}.

Reset/Block Temporary Unprotect ($\overline{RP}_F$). The Reset/Block Temporary Unprotect pin can be used to apply a Hardware Reset to the memory or to temporarily unprotect all Blocks that have been protected.

Note that if $V_{PP}/\overline{WP}$ is at V_{IL}, then the two outermost boot blocks will remain protected even if $\overline{RP}_F$ is at V_{ID}.

A Hardware Reset is achieved by holding Reset/Block Temporary Unprotect Low, V_{IL}, for at least t_{PLPX}. After Reset/Block Temporary Unprotect goes High, V_{IH}, the memory will be ready for Bus Read and Bus Write operations after t_{PHEL} or t_{RHEL}, whichever occurs last. See the M29DW640D datasheet for more details.

Holding $\overline{RP}_F$ at V_{ID} will temporarily unprotect the protected Blocks in the memory. Program and Erase operations on all blocks will be possible. The transition from V_{IH} to V_{ID} must be slower than t_{PHPHH}.

Ready/Busy Output ($\overline{RB}$). The Ready/Busy pin is an open-drain output that can be used to identify when the Flash memory is performing a Program or Erase operation. During Program or Erase operations Ready/Busy is Low, V_{OL}. Ready/Busy is high-impedance during Read mode, Auto Select mode and Erase Suspend mode.

After a Hardware Reset, Bus Read and Bus Write operations cannot begin until Ready/Busy becomes high-impedance.

The use of an open-drain output allows the Ready/Busy pins from several memories to be connected to a single pull-up resistor. A Low will then indicate that one, or more, of the memories is busy.

Byte/Word Organization Select ($\overline{BYTE}$). The Byte/Word Organization Select pin is used to switch between the x8 and x16 Bus modes of the Flash memory. When Byte/Word Organization Select is Low, V_{IL}, the Flash memory is in x8 mode, when it is High, V_{IH}, the Flash memory is in x16 mode.

SRAM Chip Enable ($\overline{E1}_S$, $E2_S$). The Chip Enable inputs activate the SRAM memory control logic, input buffers and decoders. $\overline{E1}_S$ at V_{IH} or $E2_S$ at V_{IL} deselects the memory and reduces the power consumption to the standby level. $\overline{E1}_S$ and $E2_S$ can also be used to control writing to the SRAM memory array, while $\overline{W}$ remains at V_{IL}. It is not allowed to set $\overline{E}_F$ at V_{IL}, $\overline{E1}_S$ at V_{IL} and $E2_S$ at V_{IH} at the same time.

SRAM Upper Byte Enable ($\overline{UB}_S$). The Upper Byte Enable enables the upper bytes for SRAM (DQ8-DQ15). $\overline{UB}_S$ is active low.

SRAM Lower Byte Enable ($\overline{LB}_S$). The Lower Byte Enable enables the lower bytes for SRAM (DQ0-DQ7). $\overline{LB}_S$ is active low.

V_{CCF} Supply Voltage (2.7V to 3.3V). V_{CCF} provides the power supply for all operations (Read, Program and Erase).

The Command Interface is disabled when the V_{CCF} Supply Voltage is less than the Lockout Voltage, V_{LKO}. This prevents Bus Write operations from accidentally damaging the data during power up, power down and power surges. If the Program/Erase Controller is programming or erasing during this time then the operation aborts and the memory contents being altered will be invalid.

A 0.1µF capacitor should be connected between the V_{CCF} Supply Voltage pin and the V_{SS} Ground pin to decouple the current surges from the power supply. The PCB track widths must be sufficient to carry the currents required during Program and Erase operations, I_{CC3}.

V_{CCS} Supply Voltage (2.7V to 3.3V). V_{CCS} provides the power supply for the SRAM control pins.

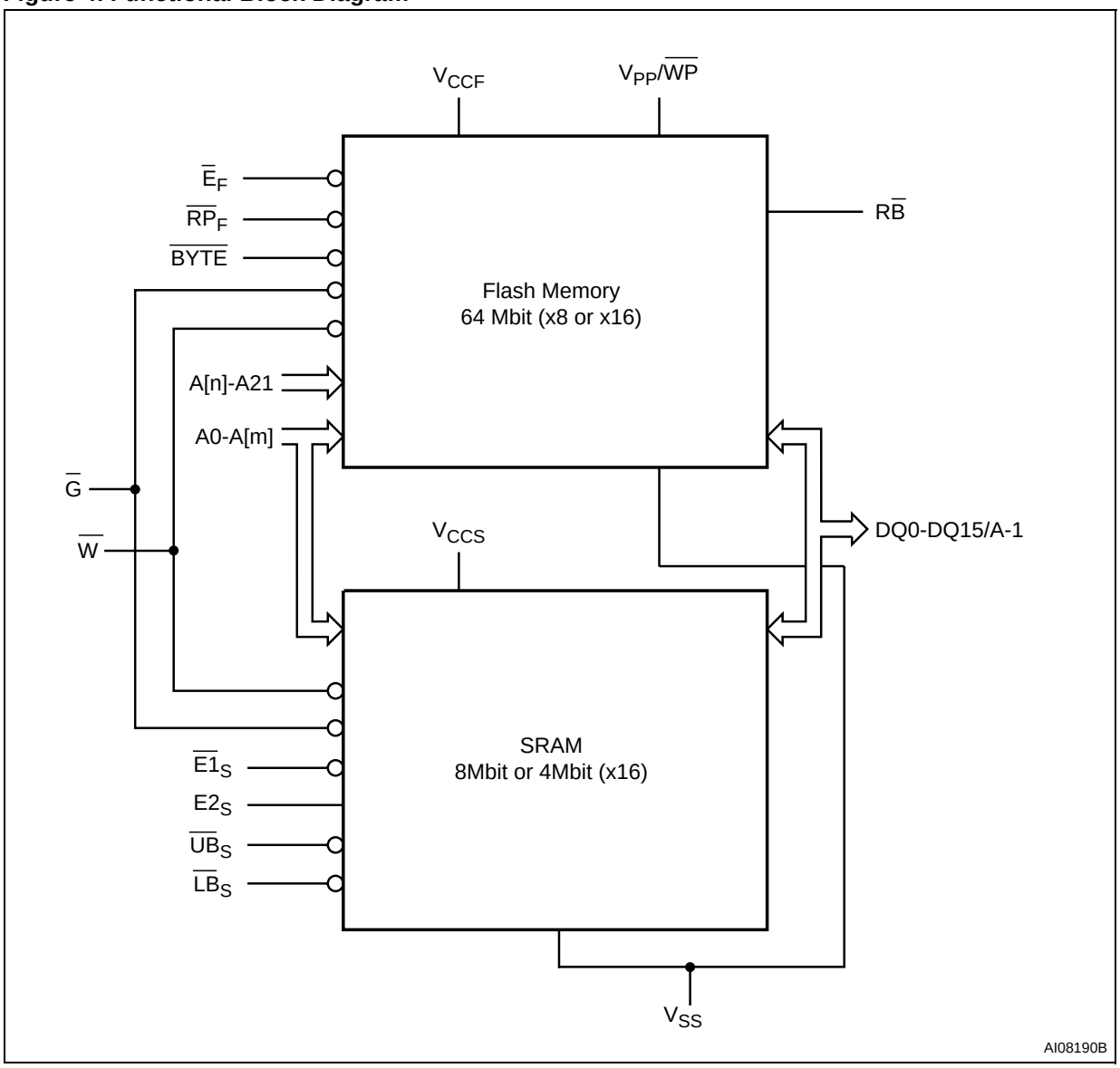
V_{SS} Ground. V_{SS} is the ground reference for all voltage measurements in the Flash and SRAM chips. The device features two V_{SS} pins both of which must be connected to the system ground.

FUNCTIONAL DESCRIPTION

The Flash and SRAM components have separate power supplies. They are distinguished by three chip enable inputs: $\overline{E}_F$ for the Flash memory and, $\overline{E1}_S$ and $E2_S$ for the SRAM.

Recommended operating conditions do not allow both the Flash and the SRAM to be in active mode at the same time. The most common example is simultaneous read operations on the Flash and the SRAM which would result in a data bus contention. Therefore it is recommended to put the SRAM in the high impedance state when reading the Flash and vice versa (see Table 2 Main Operation Modes for details).

Figure 4. Functional Block Diagram



Note: Where n=19 and m=18 for M76DW63000A, and n=18 and m=17 for M76DW62000A.

Table 2. Main Operation Modes

Operation Mode[2]		$\overline{E}_F$	$\overline{RP}_F$	$\overline{G}$	$\overline{W}$	$\overline{E1}_S$	$E2_S$	$\overline{UB}_S$	$\overline{LB}_S$	DQ15-DQ8	DQ7-DQ0
Flash Memory	Read	V_{IL}	V_{IH}	V_{IL}	V_{IH}	SRAM must be disabled				Data Output	
	Write	V_{IL}	V_{IH}	V_{IH}	V_{IL}	SRAM must be disabled				Data Input	
	Standby	V_{IH}	V_{CC} ±0.3	X	X	Any SRAM mode is allowed				Hi-Z	
	Output Disable	X	V_{IH}	V_{IH}	V_{IH}	Any SRAM mode is allowed				Hi-Z	
	Reset	X	V_{IL}	X	X	Any SRAM mode is allowed				Hi-Z	
SRAM	Read	Flash Memory must be disabled		V_{IL}	V_{IH}	V_{IL}	V_{IH}	V_{IL}	V_{IL}	Data out Word Read	
				V_{IL}	V_{IH}	V_{IL}	V_{IH}	V_{IL}	V_{IH}	Data out	Hi-Z
				V_{IL}	V_{IH}	V_{IL}	V_{IH}	V_{IH}	V_{IL}	Hi-Z	Data out
	Write	Flash Memory must be disabled		X	V_{IL}	V_{IL}	V_{IH}	V_{IL}	V_{IL}	Data in Word Write	
				X	V_{IL}	V_{IL}	V_{IH}	V_{IL}	V_{IH}	Data in	Hi-Z
				X	V_{IL}	V_{IL}	V_{IH}	V_{IH}	V_{IL}	Hi-Z	Data in
	Standby/ Power Down	Any Flash Memory mode is allowable		X	X	V_{IH}	X	X	X	Hi-Z	
				X	X	X	X	V_{IH}	V_{IH}	Hi-Z	
				X	X	X	V_{IL}	X	X	Hi-Z	
	Output Disable	Any Flash Memory mode is allowable		V_{IH}	V_{IH}	V_{IL}	V_{IH}	V_{IL}	V_{IL}	Hi-Z	
				V_{IH}	V_{IH}	V_{IL}	V_{IH}	V_{IL}	V_{IH}	Hi-Z	
				V_{IH}	V_{IH}	V_{IL}	V_{IH}	V_{IH}	V_{IL}	Hi-Z	

Note: 1. X = Don't Care = V_{IL} or V_{IH}.
2. This table is valid when $\overline{BYTE}$ = V_{IH}. This table is also valid when $\overline{BYTE}$ = V_{IL}, with the only difference that DQ15-DQ8 are always high impedance when the Flash Memory component is being accessed.
3. For the Block Protect and Unprotect features, refer to the M29DW640D datasheet. Only the In-System Technique is available in the stacked product.
4. To read the Manufacturer Code, the Device Code, the Block Protection Status and the Extended Block indicator bit, refer to the "Auto Select Command" in the M29DW640D datasheet.

MAXIMUM RATING

Stressing the device above the rating listed in the Absolute Maximum Ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 3. Absolute Maximum Ratings

Symbol	Parameter	Value		Unit
		Min	Max	
T_A	Ambient Operating Temperature (1)	–40	85	°C
T_{BIAS}	Temperature Under Bias	–50	125	°C
T_{STG}	Storage Temperature	–65	150	°C
V_{IO}	Input or Output Voltage	–0.5	V_{CCF} +0.3	V
V_{CCF}	Flash Supply Voltage	–0.6	4	V
V_{ID}	Identification Voltage	–0.6	13.5	V
V_{PPF}	Program Voltage	–0.6	13.5	V
V_{CCS}	SRAM Supply Voltage	–0.5	3.8	V

Note: 1. Depends on range.

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics Tables that follow, are derived from tests performed under the Measurement Conditions summarized in Table 4, Operating and AC Measurement Conditions. Designers should check that the operating conditions in their circuit match the measurement conditions when relying on the quoted parameters.

The operating and AC measurement parameters given in this section (see Table 4 below) correspond to those of the stand-alone Flash and SRAM devices. For compatibility purposes, the M29DW640D voltage range is restricted to V_{CCS} in the stacked product.

Table 4. Operating and AC Measurement Conditions

Parameter	Flash Memory		SRAM		Units
	70		70		
	Min	Max	Min	Max	
V_{CCF} Supply Voltage	2.7	3.6	–	–	V
V_{CCS} Supply Voltage	–	–	2.7	3.3	V
Ambient Operating Temperature	–40	85	–40	85	°C
Load Capacitance (C_L)	30		30		pF
Input Rise and Fall Times		10		3.3	ns
Input Pulse Voltages	0 to V_{CCF}		0 to V_{CCF}		V
Input and Output Timing Ref. Voltages	$V_{CCF}/2$		$V_{CCF}/2$		V

Figure 5. AC Measurement I/O Waveform

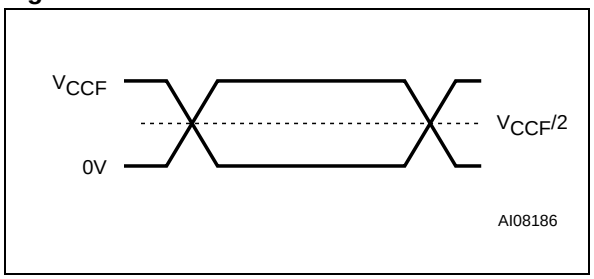


Figure 6. AC Measurement Load Circuit

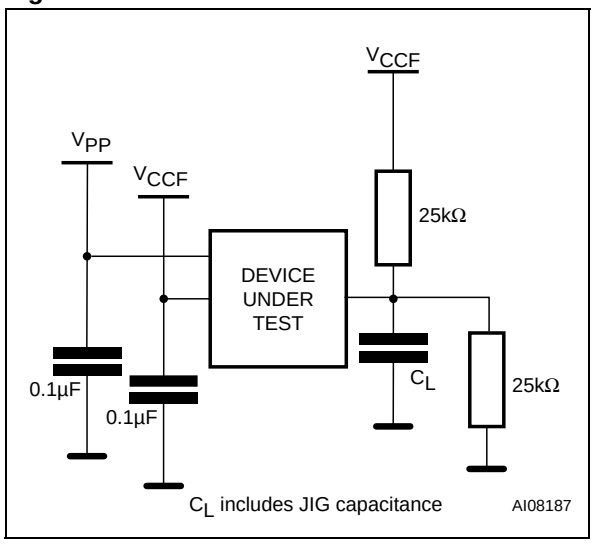


Table 5. Device Capacitance

Symbol	Parameter	Test Condition	Typ	Max	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V, f=1 MHz		12	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V, f=1 MHz		15	pF

Note: Sampled only, not 100% tested.

Table 6. Flash Memory DC Characteristics

Symbol	Parameter	Test Condition		M76DW63000A, M76DW62000A		Unit
				Min	Max	
I_{LI}	Input Leakage Current	$0V \le V_{IN} \le V_{CC}$			±1	µA
I_{LO}	Output Leakage Current	$0V \le V_{OUT} \le V_{CC}$			±1	µA
I_{CC1} (2)	Supply Current (Read)	$\overline{E}_F = V_{IL}$, $\overline{G} = V_{IH}$, f = 6MHz			10	mA
I_{CC2}	Supply Current (Standby)	$\overline{E}_F = V_{CC} \pm 0.2V$, $\overline{RP}_F = V_{CC} \pm 0.2V$			100	µA
I_{CC3} (1,2)	Supply Current (Program/ Erase)	Program/Erase Controller active	$V_{PP}/\overline{WP}$ = V_{IL} or V_{IH}		20	mA
			$V_{PP}/\overline{WP} = V_{PP}$		20	mA
V_{IL}	Input Low Voltage			–0.5	0.8	V
V_{IH}	Input High Voltage			$0.7V_{CC}$	V_{CC} +0.3	V
V_{PP}	Voltage for $V_{PP}/\overline{WP}$ Program Acceleration	V_{CC} = 3.0V ±10%		11.5	12.5	V
I_{PP}	Current for $V_{PP}/\overline{WP}$ Program Acceleration	V_{CC} = 3.0V ±10%			15	mA
V_{OL}	Output Low Voltage	I_{OL} = 1.8mA			0.45	V
V_{OH}	Output High Voltage	I_{OH} = –100µA		V_{CC} –0.4		V
V_{ID}	Identification Voltage			11.5	12.5	V
V_{LKO}	Program/Erase Lockout Supply Voltage			1.8	2.3	V

Note: 1. Sampled only, not 100% tested.
2. In Dual operations the Supply Current will be the sum of I_{CC1}(read) and I_{CC3} (program/erase).

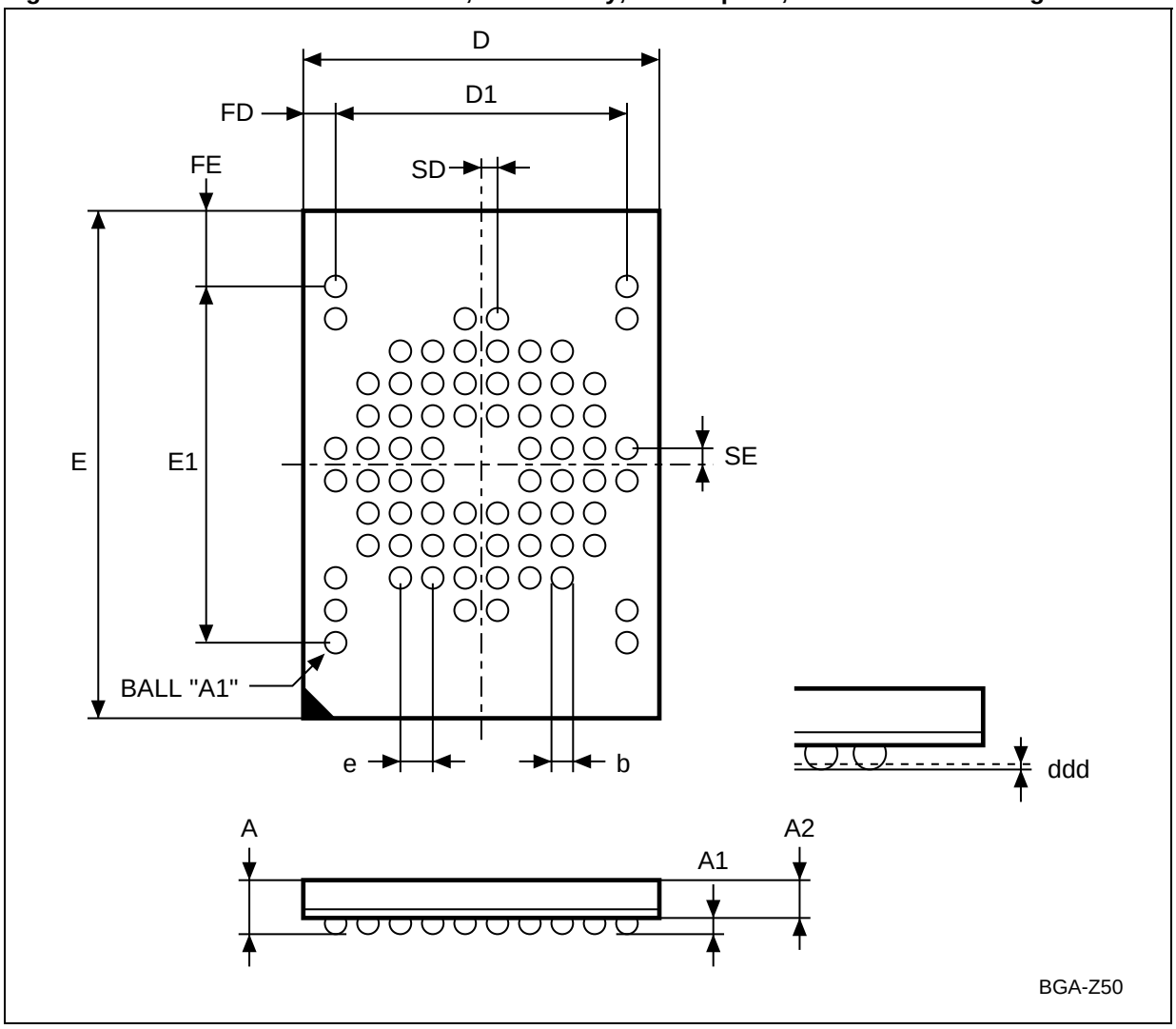
Table 7. SRAM DC Characteristics

Symbol	Parameter	Test Condition	M76DW63000A			M76DW62000A			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{LI}	Input Leakage Current	$0V \le V_{IN} \le V_{CCS}$			±1			±1	µA
I_{LO}	Output Leakage Current	$0V \le V_{OUT} \le V_{CCS}$, SRAM Outputs Hi-Z			±1			±1	µA
I_{CCS}	V_{CC} Standby Current	$\overline{E1}_S \ge V_{CCS} - 0.2V$ $V_{IN} \ge V_{CCS} - 0.2V$ or $V_{IN} \le 0.2V$ f = fmax (A0-A18[2] and DQ0-DQ15 only) f = 0 ($\overline{G}_S$, $\overline{W}_S$, $\overline{UB}_S$ and $\overline{LB}_S$)		8	25		7	15	µA
		$\overline{E1}_S \ge V_{CCS} - 0.2V$ $V_{IN} \ge V_{CCS} - 0.2V$ or $V_{IN} \le 0.2V$, f = 0		8	25		7	15	µA
I_{CC}	Supply Current	f = fmax = $1/_{AVAV}$, V_{CCS} = 3.3V, I_{OUT} = 0 mA		5.5	12		5.5	12	mA
		f = 1MHz, V_{CCS} = 3.3V, I_{OUT} = 0 mA		1.5	3		1.5	3	mA
V_{IL}	Input Low Voltage		–0.3		0.8	–0.3		0.8	V
V_{IH}	Input High Voltage		2.2		V_{CCS} +0.3	2.2		V_{CCS} +0.3	V
V_{OL}	Output Low Voltage	$V_{CCS} = V_{CC}$ min I_{OL} = 2.1mA			0.4			0.4	V
V_{OH}	Output High Voltage	$V_{CCS} = V_{CC}$ min I_{OH} = –1.0mA	2.4			2.4			V

Note: 1. Sampled only, not 100% tested.
2. A0-A18 for the M76DW63000A, A0-A17 for the M76DW62000A.

PACKAGE MECHANICAL

Figure 7. Stacked LFBGA73 8x11.6mm, 10x12 array, 0.8mm pitch, Bottom View Package Outline



Note: Drawing is not to scale.

Table 8. Stacked LFBGA73 8x11.6mm, 10x12 array, 0.8mm pitch, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.400			0.0551
A1		0.250			0.0098	
A2	0.910			0.0358		
b	0.400	0.350	0.450	0.0157	0.0138	0.0177
D	8.000	7.900	8.100	0.3150	0.3110	0.3189
D1	7.200			0.2835		
ddd			0.100			0.0039
E	11.600	11.500	11.700	0.4567	0.4528	0.4606
E1	8.800			0.3465		
e	0.800	–	–	0.0315	–	–
FD	0.400			0.0157		
FE	1.400			0.0551		
SD	0.400	–	–	0.0157	–	–
SE	0.400	–	–	0.0157	–	–

PART NUMBERING

Table 9. Ordering Information Scheme

Example: M76DW6 2 0 0 0 A 70 Z T

Device Type
M76 = MMP (Flash + SRAM)

Architecture
D = Dual Operation

Operating Voltage
W = V_{CCF} = V_{CCS} = 2.7V to 3.3V

Flash Device Size (Die1 Density)
6 = 64 Mbit

SRAM Device Size (Die2 Density)
2 = 4 Mbit
3 = 8 Mbit

Die3
0 = Die3 Density

Die4
0 = Die4 Density

Flash Specification Details
0 = Multiple Bank

Stacked Specification Details
A = 0.15µm Flash & SRAM

Speed
70 = 70ns
90 = 90ns

Package and Temperature Range
Z = LFBGA73: 8 x 11.6mm, 0.8mm pitch

Option
T = Tape & Reel packing

Note: This product is also available with the Extended Block factory locked. For further details and ordering information contact your nearest ST sales office.

Devices are shipped from the factory with the memory content bits erased to ’1’.
For a list of available options (Speed, Package, etc.) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

FLASH MEMORY DEVICE

The M76DW62000A contains one 64 Mbit Flash memory. For detailed information on how to use the Flash memory refer to the M29DW640D datasheet, which is available on the STMicroelectronics web site, www.st.com.

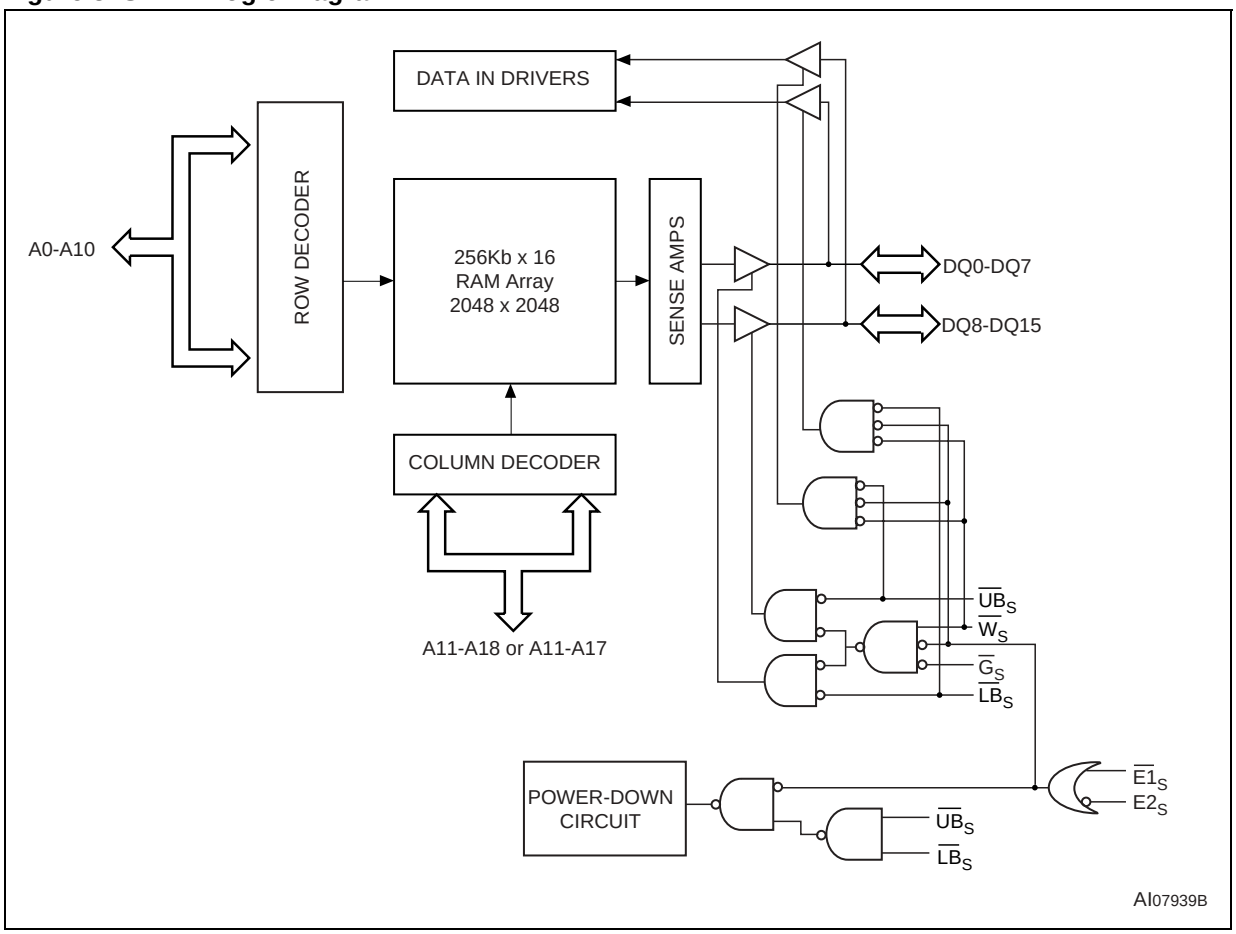
SRAM DEVICE

SRAM SUMMARY DESCRIPTION

The SRAM is an 8Mbit or 4Mbit asynchronous random access memory which features a super low voltage operation and low current consumption with an access time of 70ns under all conditions.

The memory operations can be performed using a single low voltage supply, 2.7V to 3.3V, which is the same as the Flash voltage supply.

Figure 8. SRAM Logic Diagram



SRAM OPERATIONS

There are five standard operations that control the SRAM component. These are Bus Read, Bus Write, Standby/Power-down, Data Retention and Output Disable. A summary is shown in Table 2, Main Operation Modes

Read. Read operations are used to output the contents of the SRAM Array. The SRAM is in Read mode whenever Write Enable, $\overline{W}_S$, is at V_{IH}, Output Enable, $\overline{G}_S$, is at V_{IL}, Chip Enable, $\overline{E1}_S$, is at V_{IL}, Chip Enable, $E2_S$, is at V_{IH}, and Byte Enable inputs, $\overline{UB}_S$ and $\overline{LB}_S$ are at V_{IL}.

Valid data will be available on the output pins after a time of t_{AVQV} after the last stable address. If the Chip Enable or Output Enable access times are not met, data access will be measured from the limiting parameter (t_{E1LQV}, t_{E2HQV}, or t_{GLQV}) rather than the address. Data out may be indeterminate at t_{E1LQX}, t_{E2HQX} and t_{GLQX}, but data lines will always be valid at t_{AVQV} (see Table 10, Table 10, Figures 9 and 10, SRAM Read AC Characteristics).

Write. Write operations are used to write data to the SRAM. The SRAM is in Write mode whenever $\overline{W}$ and $\overline{E1}_S$ are at V_{IL}, and $E2_S$ is at V_{IH}. Either the Chip Enable inputs, $\overline{E1}_S$ and $E2_S$, or the Write Enable input, $\overline{W}_S$, must be deasserted during address transitions for subsequent write cycles.

A Write operation is initiated when $\overline{E1}_S$ is at V_{IL}, $E2_S$ is at V_{IH} and $\overline{W}$ is at V_{IL}. The data is latched on the falling edge of $\overline{E1}_S$, the rising edge of $E2_S$ or the falling edge of $\overline{W}_S$, whichever occurs last. The Write cycle is terminated on the rising edge of $\overline{E1}_S$, the rising edge of $\overline{W}$ or the falling edge of $E2_S$, whichever occurs first.

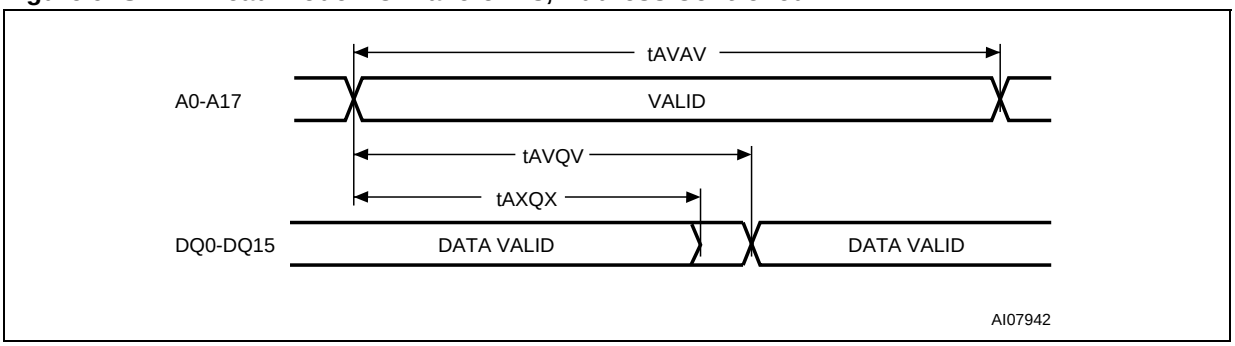
If the Output is enabled ($\overline{E1}_S=V_{IL}$, $E2_S=V_{IH}$ and $\overline{G}_S=V_{IL}$), then $\overline{W}$ will return the outputs to high impedance within t_{WLQZ} of its falling edge. Care must be taken to avoid bus contention in this type of operation. The Data input must be valid for t_{DVWH} before the rising edge of Write Enable, for t_{DVE1H} before the rising edge of $\overline{E1}_S$ or for t_{DVE2L} before the falling edge of $E2_S$, whichever occurs first, and remain valid for t_{WHDX}, t_{E1HAX} or t_{E2LAX} (see Table 11, SRAM Write AC Characteristics, Figures 12, 13, 14 and 15).

Standby/Power-Down. The SRAM component has a chip enabled power-down feature which invokes an automatic standby mode (see Table 10, SRAM Read AC Characteristics, Figure 11, SRAM Standby AC Waveforms). The SRAM is in Standby mode whenever either Chip Enable is deasserted, $\overline{E1}_S$ at V_{IH} or $E2_S$ at V_{IL}. It is also possible when UB_S and LB_S are at V_{IH}.

Data Retention. The SRAM data retention performance as V_{CCS} goes down to V_{DR} are described in Table 12, SRAM Low V_{CCS} Data Retention Characteristic, and Figure 16, SRAM Low V_{CCS} Data Retention AC Waveforms, $E1_S$ or UB_S / LB_S Controlled. In $\overline{E1}_S$ controlled data retention mode, the minimum standby current mode is entered when $\overline{E1}_S \geq V_{CCS} - 0.2V$ and $E2_S \leq 0.2V$ or $E2_S \geq V_{CCS} - 0.2V$. In $E2_S$ controlled data retention mode, minimum standby current mode is entered when $E2_S \leq 0.2V$.

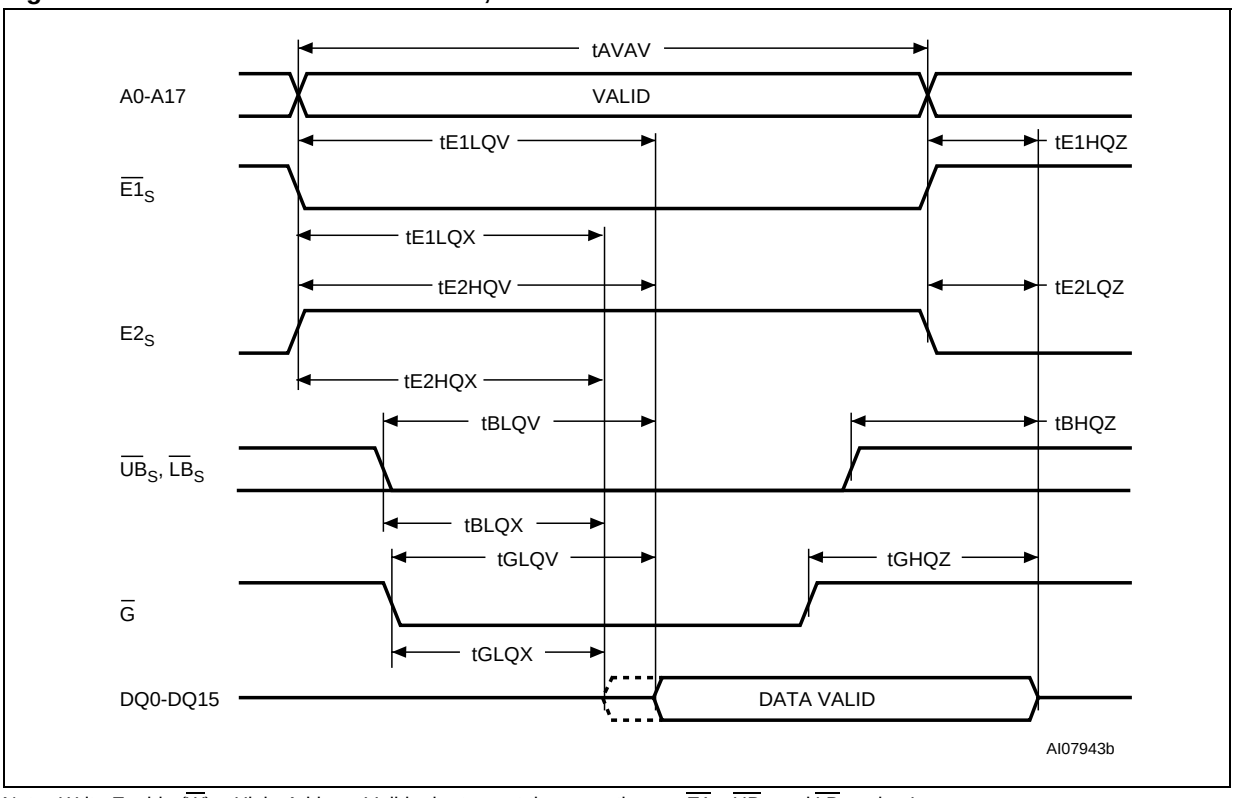
Output Disable. The data outputs are high impedance when the Output Enable, $\overline{G}_S$, is at V_{IH} with Write Enable, $\overline{W}_S$, at V_{IH}.

Figure 9. SRAM Read Mode AC Waveforms, Address Controlled



Note: $\overline{E1}_S$ = Low, $E2_S$ = High, $\overline{G}$ = Low, $\overline{UB}_S$ and/or $\overline{LB}_S$ = High, $\overline{W}$ = High.

Figure 10. SRAM Read AC Waveforms, $\overline{G}$ Controlled



Note: Write Enable ($\overline{W}$) = High. Address Valid prior to or at the same time as $\overline{E1}_S$, $\overline{UB}_S$ and $\overline{LB}_S$ going Low.

Figure 11. SRAM Standby AC Waveforms

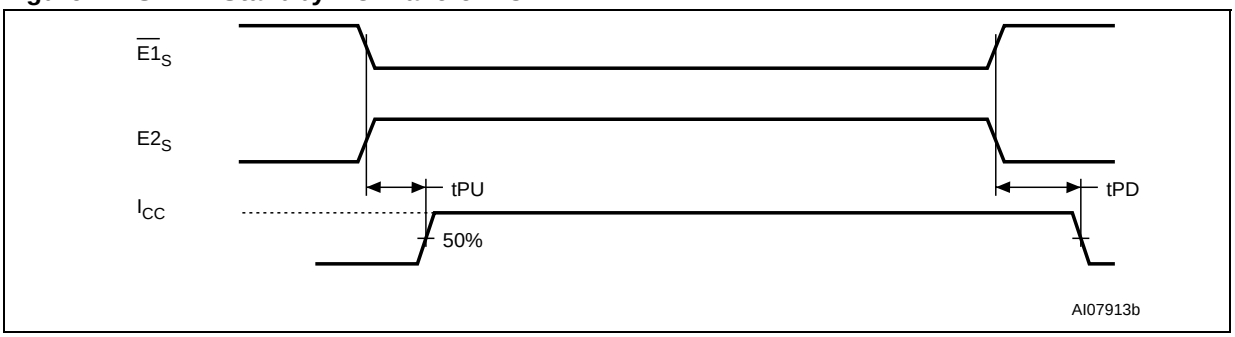
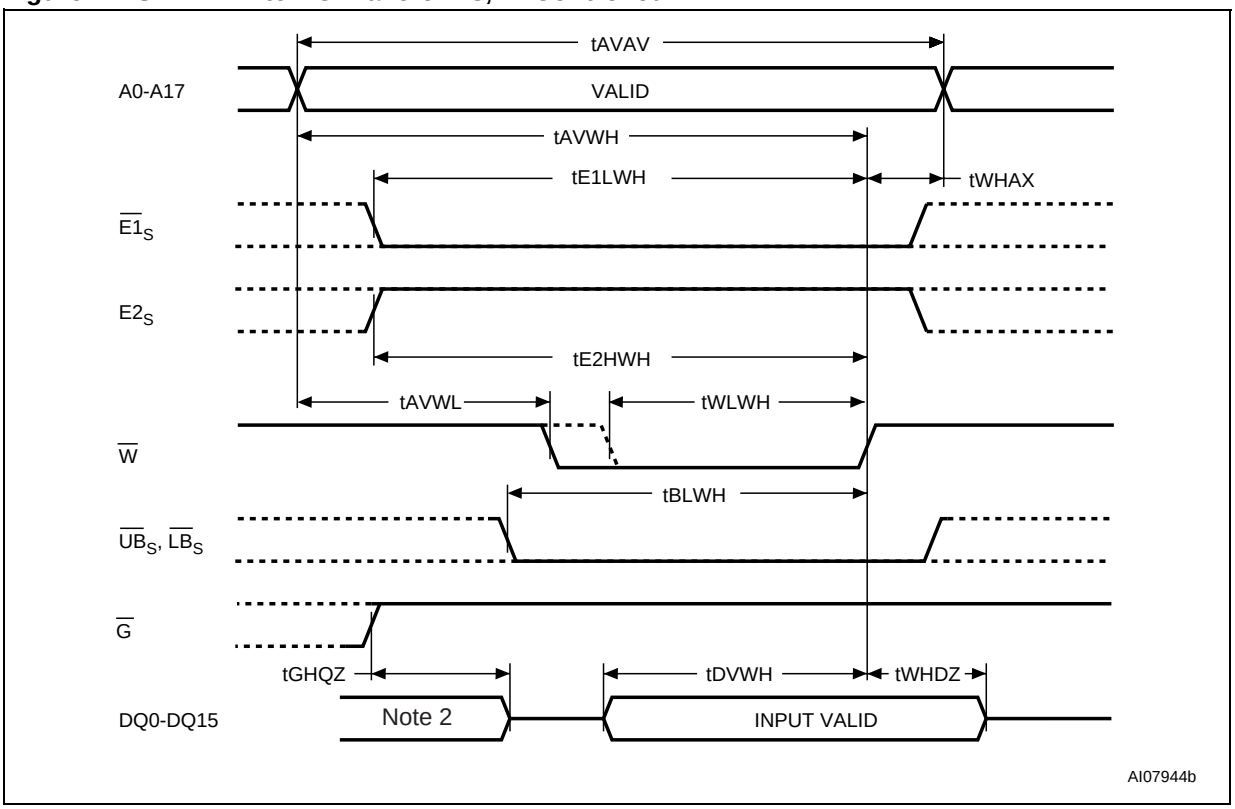


Table 10. SRAM Read AC Characteristics

Symbol	Alt	Parameter	SRAM		Unit
			Min	Max	
t_{AVAV}	t_{RC}	Read Cycle Time	70		ns
t_{AVQV}	t_{ACC}	Address Valid to Output Valid		70	ns
t_{AXQX}	t_{OH}	Address Transition to Output Transition	10		ns
t_{BHQZ}	t_{BHZ}	$\overline{UB}_S$, $\overline{LB}_S$ Disable to Hi-Z Output		25	ns
t_{BLQV}	t_{AB}	$\overline{UB}_S$, $\overline{LB}_S$ Access Time		70	ns
t_{BLQX}	t_{BLZ}	$\overline{UB}_S$, $\overline{LB}_S$ Enable to Low-Z Output	5		ns
t_{E1LQV} t_{E2HQV}	t_{ACS1}	Chip Enable 1 Low or Chip Enable 2 High to Output Valid		70	ns
t_{E1LQX} t_{E2HQX}	t_{CLZ1}	Chip Enable 1 Low or Chip Enable 2 High to Output Transition	10		ns
t_{E1HQZ} t_{E2LQZ}	t_{HZCE}	Chip Enable High or Chip Enable 2 Low to Output Hi-Z		25	ns
t_{GHQZ}	t_{OHZ}	Output Enable High to Output Hi-Z		25	ns
t_{GLQV}	t_{OE}	Output Enable Low to Output Valid		35	ns
t_{GLQX}	t_{OLZ}	Output Enable Low to Output Transition	5		ns
t_{PD} (1)		Chip Enable 1 High or Chip Enable 2 Low to Power Down		70	ns
t_{PU} (1)		Chip Enable 1 Low or Chip Enable 2 High to Power Up	0		ns

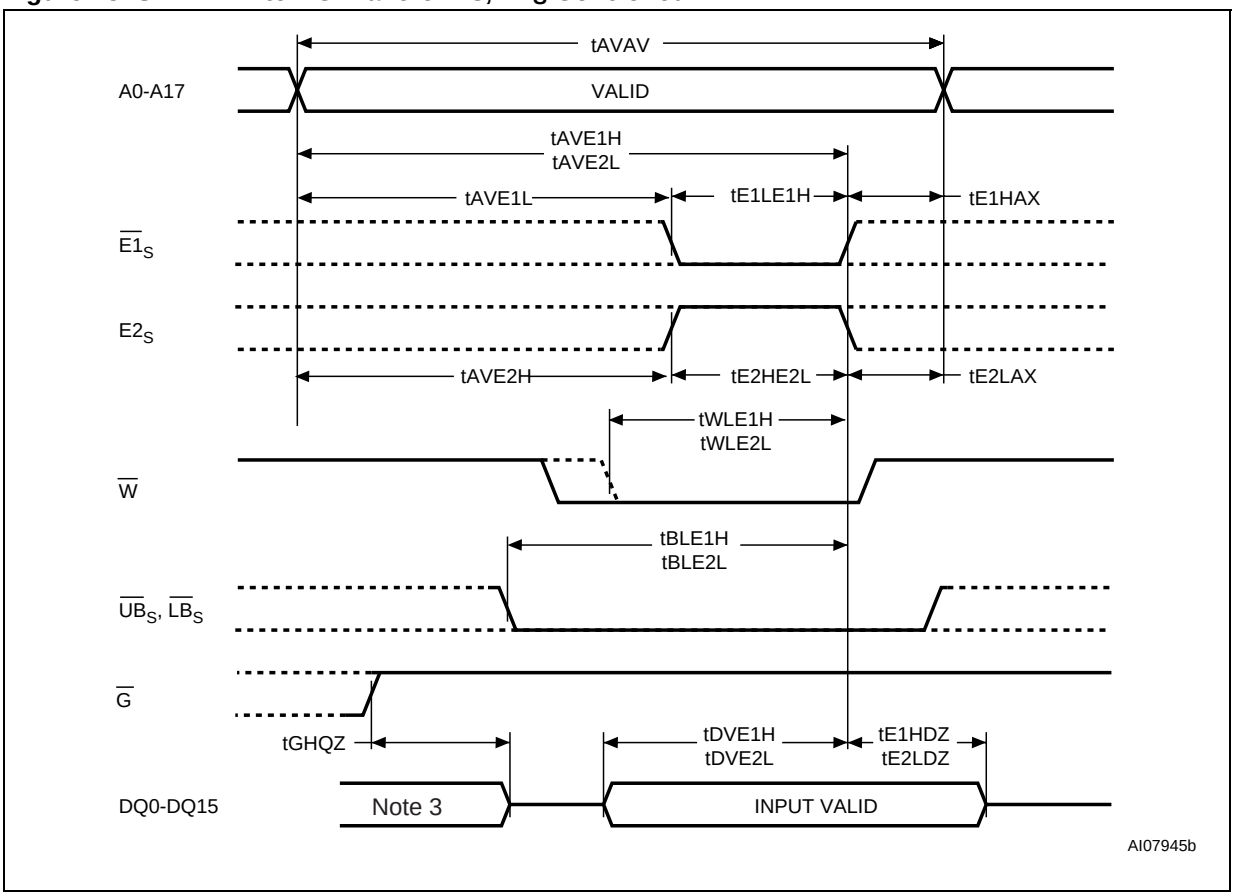
Note: 1. Sampled only. Not 100% tested.

Figure 12. SRAM Write AC Waveforms, $\overline{W}$ Controlled



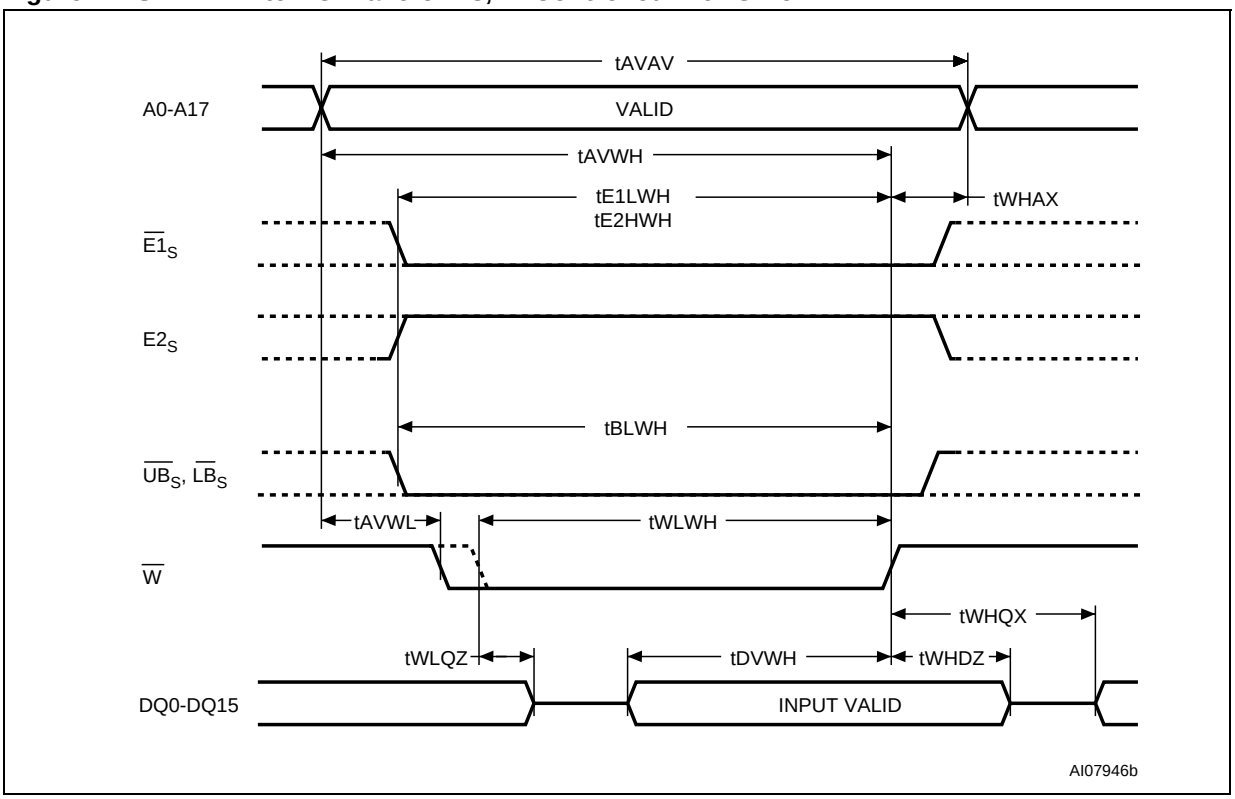
Note: 1. $\overline{W}$, $\overline{E1}_S$, $E2_S$, $\overline{UB}_S$ and/or LB_S must be asserted to initiate a write cycle. Output Enable ($\overline{G}$) = Low (otherwise, DQ0-DQ15 are high impedance). If $\overline{E1}_S$, $E2_S$ and $\overline{W}$ are deasserted at the same time, DQ0-DQ15 remain high impedance.
2. The I/O pins are in output mode and input signals must not be applied.

Figure 13. SRAM Write AC Waveforms, $\overline{E1}_S$ Controlled



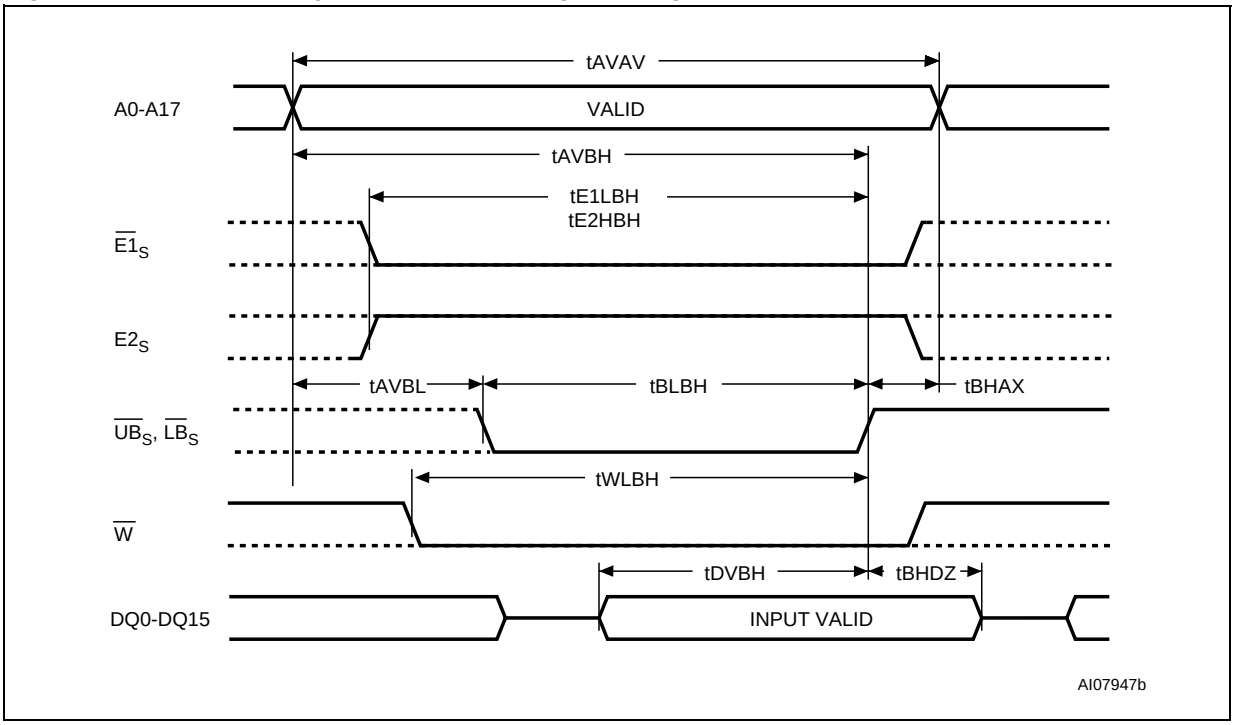
Note: 1. $\overline{W}_S$, $\overline{E1}_S$, $E2_S$, $\overline{UB}_S$ and/or LB_S must be asserted to initiate a write cycle. Output Enable ($\overline{G}_S$) = Low (otherwise, DQ0-DQ15 are high impedance). If $\overline{E1}_S$, $E2_S$ and $\overline{W}$ are deasserted at the same time, DQ0-DQ15 remain high impedance.
2. If $\overline{E1}_S$, $E2_S$ and $\overline{W}$ are deasserted at the same time, DQ0-DQ15 remain high impedance.
3. The I/O pins are in output mode and input signals must not be applied.

Figure 14. SRAM Write AC Waveforms, $\overline{W}$ Controlled with $\overline{G}$ Low



Note: 1. If $\overline{E1}_S$, $E2_S$ and $\overline{W}$ are deasserted at the same time, DQ0-DQ15 remain high impedance.

Figure 15. SRAM Write Cycle Waveform, $\overline{UB}_S$ and $\overline{LB}_S$ Controlled, $\overline{G}$ Low



Note: 1. If $\overline{E1}_S$, $E2_S$ and $\overline{W}$ are deasserted at the same time, DQ0-DQ15 remain high impedance.

Table 11. SRAM Write AC Characteristics

Symbol	Alt	Parameter	SRAM		Unit
			Min	Max	
t_{AVAV}	t_{WC}	Write Cycle Time	70		ns
t_{AVE1L}, t_{AVE2H}, t_{AVWL}, t_{AVBL}	t_{AS}	Address Valid to Beginning of Write	0		ns
t_{AVE1H}, t_{AVE2L}	t_{AW}	Address Valid to Chip Enable 1 Low or Chip Enable 2 High	60		ns
t_{AVWH}	t_{AW}	Address Valid to Write Enable High	60		ns
t_{BLWH} t_{BLE1H} t_{BLE2L} t_{AVBH}	t_{BW}	$\overline{UB}_S$, $\overline{LB}_S$ Valid to End of Write	60		ns
t_{BLBH}	t_{BW}	$\overline{UB}_S$, $\overline{LB}_S$ Low to $\overline{UB}_S$, $\overline{LB}_S$ High	60		ns
t_{DVE1H}, t_{DVE2L}, t_{DVWH} t_{DVBH}	t_{DW}	Input Valid to End of Write	30		ns
t_{E1HAX}, t_{E2LAX}, t_{WHAX} t_{BHAX}	t_{WR}	End of Write to Address Change	0		ns
t_{E1HDZ}, t_{E2LDZ}, t_{WHDZ} t_{BHDZ}	t_{HD}	Address Transition to End of Write	0		ns
t_{E1LE1H}, t_{E1LBH} t_{E1LWH}	t_{CW1}	Chip Enable 1 Low to End of Write	60		ns
t_{E2HE2L}, t_{E2HBH}, t_{E2HWH}	t_{CW2}	Chip Enable 2 High to End of Write	60		ns
t_{GHQZ}	t_{GHZ}	Output Enable High to Output Hi-Z		25	ns
t_{WHQX}	t_{DH}	Write Enable High to Input Transition	5		ns
t_{WLBH}	t_{WP}	Write Enable Low to $\overline{UB}_S$, $\overline{LB}_S$ High	50		ns
t_{WLQZ}	t_{WHZ}	Write Enable Low to Output Hi-Z		25	ns
t_{WLWH} t_{WLE1H} t_{WLE2L}	t_{WP}	Write Enable Pulse Width	50		ns

Figure 16. SRAM Low V_{CCS} Data Retention AC Waveforms, $\overline{E1}_S$ or $\overline{UB}_S$ / $\overline{LB}_S$ Controlled

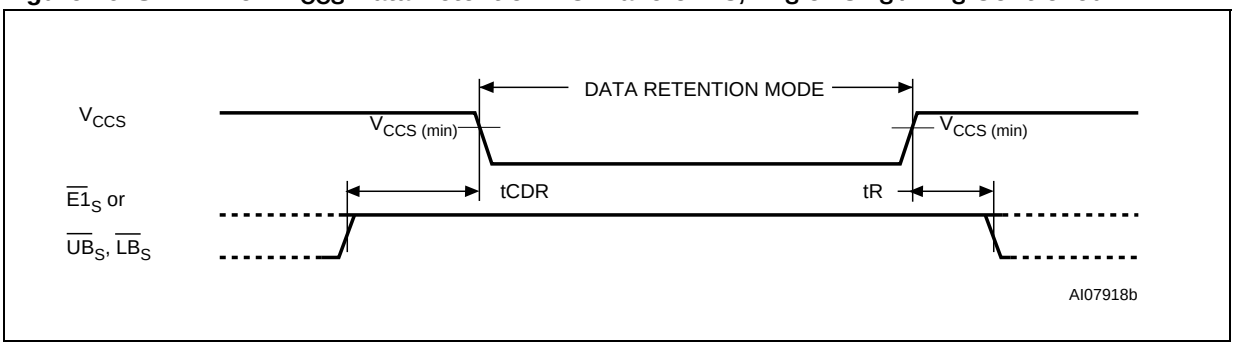


Table 12. SRAM Low V_{CCS} Data Retention Characteristic

Symbol	Parameter	Test Condition	M76DW63000A			M76DW62000A			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{CCDR}	Supply Current (Data Retention)	V_{CCS} = 1.5V, $\overline{E1}_S \geq V_{CCS} - 0.2V$, $V_{IN} \geq V_{CCS} - 0.2V$ or $V_{IN} \leq 0.2V$		4	12		3	10	µA
V_{DR}	Supply Voltage (Data Retention)		1.5		3.3	1.5		3.3	V
t_{CDR}	Chip Disable to Power Down		0			0			ns
t_R	Operation Recovery Time		70			70			ns

2. Sampled only. Not 100% tested.

REVISION HISTORY

Table 13. Document Revision History

Date	Version	Revision Details
16-Apr-2003	1.0	First Issue
19-May-2003	1.1	M76DW63000A, 8Mbit SRAM, added
12-Jun-2003	1.2	M76DW63000A, 8Mbit SRAM, corrected to 512Kx16 on first page
24-Sep-2003	1.3	Voltage supply range extended 2.7V working at all speed options